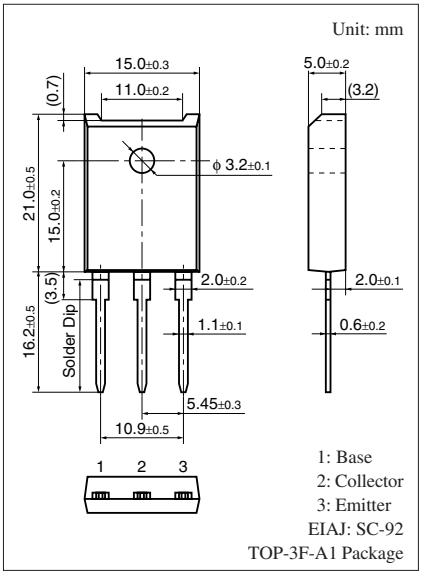
2SD1705

Silicon NPN epitaxial planar type

For power switching
Complementary to 2SB1154



■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Large collector current I_C
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	130	V
Collector-emitter voltage (Base open)	V_{CEO}	80	V
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Collector current	I_C	10	A
Peak collector current	I_{CP}	20	A
Collector power dissipation	P_C	70	W
$T_a = 25°C$		3.0	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

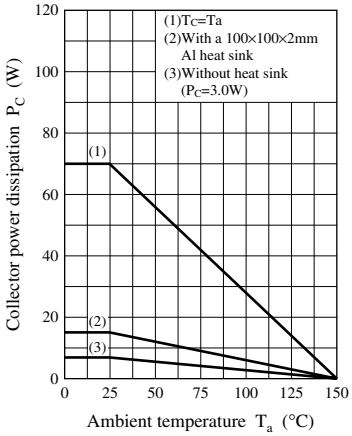
■ Electrical Characteristics $T_C = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	I_C = 10 mA, I_B = 0	80			V
Collector-base cutoff current (Emitter open)	I_{CBO}	V_{CB} = 100 V, I_E = 0			10	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	V_{EB} = 5 V, I_C = 0			50	μA
Forward current transfer ratio	h_{FE1}	V_{CE} = 2 V, I_C = 0.1 A	45			—
	h_{FE2} *	V_{CE} = 2 V, I_C = 3 A	90		260	
	h_{FE3}	V_{CE} = 2 V, I_C = 6 A	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	I_C = 6 A, I_B = 0.3 A			0.5	V
	$V_{CE(sat)2}$	I_C = 10 A, I_B = 1 A			1.5	
Base-emitter saturation voltage	$V_{BE(sat)1}$	I_C = 6 A, I_B = 0.3 A			1.5	V
	$V_{BE(sat)2}$	I_C = 10 A, I_B = 1 A			2.5	
Transition frequency	f_T	V_{CE} = 10 V, I_C = 0.5 A, f = 1 MHz		20		MHz
Turn-on time	t_{on}	I_C = 6 A, I_{B1} = 0.6 A, I_{B2} = − 0.6 A		0.5		μs
Storage time	t_{stg}	V_{CC} = 50 V		2.0		μs
Fall time	t_f			0.2		μs

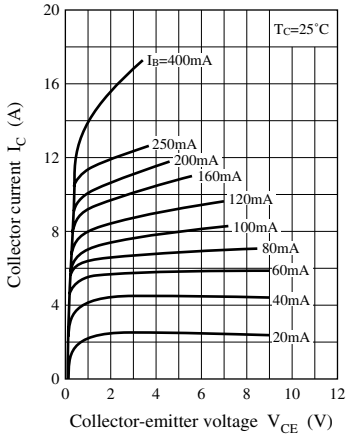
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *: Rank classification

Rank	Q	P
h_{FE2}	90 to 180	130 to 260

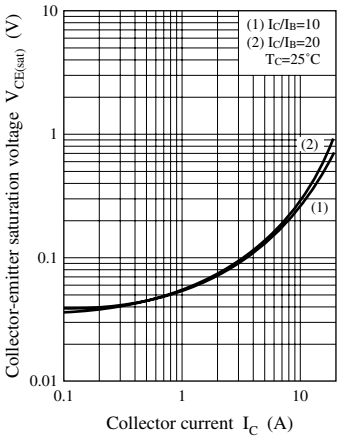
P_C — T_a



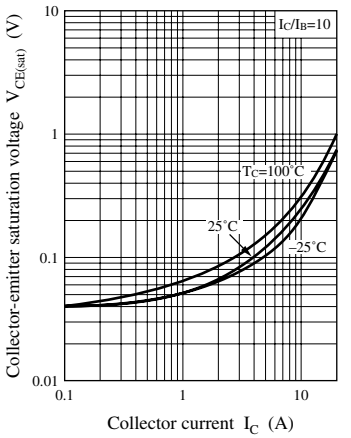
I_C — V_{CE}



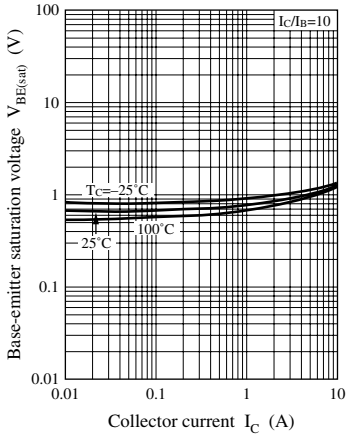
$V_{CE(sat)}$ — I_C



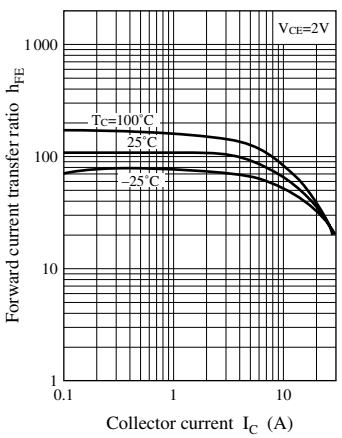
$V_{CE(sat)}$ — I_C



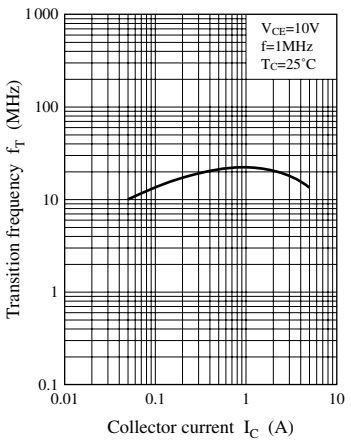
$V_{BE(sat)}$ — I_C



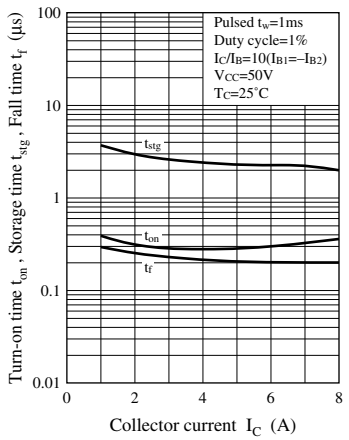
h_{FE} — I_C



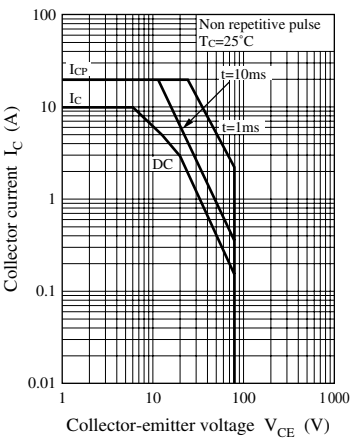
f_T — I_C



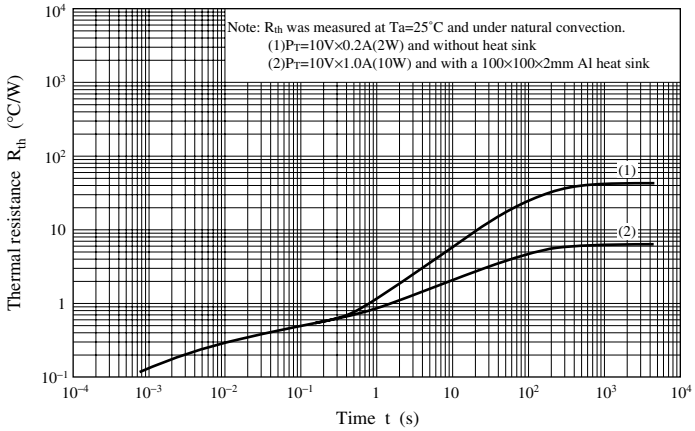
t_{on} , t_{stg} , t_f — I_C



Safe operation area



R_{th} — t


Note: Rth was measured at Ta=25°C and under natural convection.
(1)PT=10V×0.2A(2W) and without heat sink
(2)PT=10V×1.0A(10W) and with a 100×100×2mm Al heat sink
(1)
(2)
Thermal resistance Rth (°C/W)
Time t (s)
10^4
10^3
10^2
10
1
10^−1
10^−4
10^−3
10^−2
10^−1
1
10
10^2
10^3
10^4

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